Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application. Please amend claims 80, 81, 84, 88, 89, 92, 95-101, and 104-110 as follows:

Listing of Claims:

1-79. (Cancelled)

80. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer ~~onto~~ over the wafer;

~~exposing the wafer in situ to a reducing environment;~~

depositing a second conductive layer over the wafer;

exposing the second conductive layer in situ to a reducing environment; and

exposing the second conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

81. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer ~~onto~~ over the wafer;

~~exposing the wafer in situ to a reducing environment~~;

depositing a second conductive layer over wafer;

exposing the first conductive layer in situ to a reducing environment; and

exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl, wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

82. (Previously Presented) The method of claim 80 further comprising forming a third conductive layer on the second conductive layer.

83. (Previously Presented) The method of claim 82 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

84. (Currently Amended) The method of claim 83 wherein ~~the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and~~ the third conductive layer comprises polysilicon.

85-87. (Cancelled)

88. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer ~~onto~~ over the wafer;

~~exposing the wafer to a reducing environment;~~

depositing a second conductive layer over the wafer;

exposing the second conductive layer to a reducing environment; and

passivating the second conductive layer by exposing the second conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl, wherein the first conductive layer comprises hemispherical silicon grain and wherein the second conductive layer comprises tungsten nitride.

89. (Currently Amended) A method of treating a wafer, comprising:

depositing a first conductive layer ~~onto~~ over the wafer;

~~exposing the wafer to a reducing environment;~~

depositing a second conductive layer over the wafer;

exposing the first conductive layer to a reducing environment; and

passivating the first conductive layer by exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl, wherein the first conductive layer comprises tungsten nitride and wherein the second conductive layer comprises polysilicon.

90. (Previously Presented) The method of claim 88 further comprising forming a third conductive layer on the second conductive layer.

91. (Previously Presented) The method of claim 90 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

92. (Currently Amended) The method of claim 91 wherein ~~the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and~~ the third conductive layer comprises polysilicon.

93. (Previously Presented) The method of claim 81 further comprising forming a third conductive layer on the second conductive layer.

94. (Previously Presented) The method of claim 93 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

95. (Currently Amended) The method of claim 94 wherein ~~the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and~~ the third conductive layer comprises polysilicon.

96. (Currently Amended) The method of claim 81 wherein exposing the ~~wafer~~ first conductive layer in situ to a reducing environment comprises exposing the ~~wafer~~ first conductive layer to silane gas.

97. (Currently Amended) The method of claim 81 wherein exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl comprises exposing the first conductive layer to this selection prior to exposing the ~~wafer~~ first conductive layer in situ to a reducing environment.

98. (Currently Amended) The method of claim 81 wherein exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl comprises exposing the first conductive layer to this selection prior to depositing the second conductive layer.

99. (Currently Amended) The method of claim 80 wherein exposing the ~~wafer~~ second conductive layer in situ to a reducing environment comprises exposing the ~~wafer~~ second conductive layer to silane gas.

100. (Currently Amended) The method of claim 80 wherein exposing the second conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl comprises exposing the second conductive layer to this selection prior to exposing the ~~wafer~~ second conductive layer in situ to a reducing environment.

101. (Currently Amended) The method of claim 80 wherein exposing the second conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCl comprises exposing the second conductive layer to this selection prior to depositing the ~~second~~ first conductive layer.

102. (Previously Presented) The method of claim 89 further comprising forming a third conductive layer on the second conductive layer.

103. (Previously Presented) The method of claim 102 further comprising forming a borophosphosilicate glass layer on the third conductive layer.

104. (Currently Amended) The method of claim 103 wherein ~~the first conductive layer comprises hemispherical silicon grain, the second conductive layer comprises tungsten nitride, and~~ the third conductive layer comprises polysilicon.

105. (Currently Amended) The method of claim 89 wherein exposing the ~~wafer~~ first conductive layer to a reducing environment comprises exposing the ~~wafer~~ first conductive layer to silane gas.

106. (Currently Amended) The method of claim 89 wherein exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCL comprises exposing the first conductive layer to this selection prior to exposing the ~~wafer~~ first conductive layer to a reducing environment.

107. (Currently Amended) The method of claim 89 wherein exposing the first conductive layer to a material ~~selected from the group consisting of diborane and~~ comprising HCL comprises exposing the first conductive layer to this selection prior to depositing the second conductive layer.

108. (Currently Amended) The method of claim 88 wherein exposing the ~~wafer~~ second conductive layer to a reducing environment comprises exposing the ~~wafer~~ second conductive layer to silane gas.

109. (Currently Amended) The method of claim 88 wherein exposing the second conductive layer to a material ~~selected from the group consisting of diborane, and~~ comprising HCl comprises exposing the ~~wafer~~ second conductive layer to this selection prior to exposing the second conductive layer to a reducing environment.

110. (Currently Amended) The method of claim 88 wherein exposing the ~~wafer~~ second conductive layer to a material ~~selected from the group consisting of diborane, and~~ comprising HCl comprises exposing the ~~wafer~~ second conductive layer to this selection prior to depositing the ~~second~~ first conductive layer.